Discrete POWER & Signal **Technologies**

2N5770

FAIRCHILD SEMICONDUCTOR TM

2N5770



NPN RF Transistor

This device is designed for use as RF amplifiers, oscillators and multipliers with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 43. See PN918 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	15	V
V _{CBO}	Collector-Base Voltage	30	V
V_{EBO}	Emitter-Base Voltage	4.5	V
Ic	Collector Current - Continuous	50	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES: 1) These ratings are based on a maximum junction temperature of 150 degrees C. 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted				
Symbol	Characteristic	Мах	Units	
		2N5770		
P _D	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C	
$R_{\theta_{JC}}$	Thermal Resistance, Junction to Case	125	°C/W	
R _{eJA}	Thermal Resistance, Junction to Ambient	357	°C/W	

NPN RF Transistor

(continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 3.0 \text{ mA}, I_{\rm B} = 0$	15		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{C} = 1.0 \ \mu A, I_{E} = 0$	30		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu {\rm A}, I_{\rm C} = 0$	4.5		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 15 \text{ V}, \text{ I}_{E} = 0$		10	nA
		$V_{CB} = 15 \text{ V}, \text{ I}_{E} = 0, \text{ T}_{A} = 150 \text{ °C}$		1.0	μA
EBO	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_C = 0$ $V_{EB} = 2.0 \text{ V}, I_C = 0$		10 1.0	μΑ μΑ
					μι
	RACTERISTICS*	$V_{CE} = 1.0 \text{ V}, I_{C} = 3.0 \text{ mA}$	20		
IFE	De cullent Gain	$V_{CE} = 1.0 \text{ V}, I_C = 3.0 \text{ mA}$ $V_{CE} = 10 \text{ V}, I_C = 8.0 \text{ mA}$	20 50	200	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 10$ mA, $I_{\rm B} = 1.0$ mA		0.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA}$		1.0	V
NF	Noise Figure	I_{c} = 1.0 mA, V_{cE} = 8.0 V, f = 60 MHz, Rg = 400 Ω		6.0	dB
C _{cb}	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1.0 \text{ MHz}$	0.7	1.1	pF
Cib	Input Capacitance	V _{EB} = 0.5 V		2.0	pF
h _{fe}	Small-Signal Current Gain	$ I_{C} = 8.0 \text{ mA}, V_{CE} = 10 \text{ V}, $ f = 100 MHz I_{C} = 8.0 mA, V_{CE} = 10 \text{ V},	9.0	18	
		f = 1.0 kHz	40	240	
rb'C _c	Collector-Base Time Constant	f = 1.0 kHz I _E = 8.0 mA, V _{CB} = 10 V,	40 3.0	240 20	pS
rb'C _C	Collector-Base Time Constant	f = 1.0 kHz			pS
-		f = 1.0 kHz I _E = 8.0 mA, V _{CB} = 10 V,			pS
FUNCTIC	Collector-Base Time Constant	f = 1.0 kHz I _E = 8.0 mA, V _{CB} = 10 V,			pS dB
FUNCTIC G _{pe}	NAL TEST		3.0		
rb'C _c FUNCTIC G _{pe} Po η	NAL TEST Amplifier Power Gain	$\begin{array}{l} f = 1.0 \text{ kHz} \\ I_{E} = 8.0 \text{ mA}, \text{ V}_{CB} = 10 \text{ V}, \\ f = 79.8 \text{ MHz} \end{array}$ $I_{C} = 6.0 \text{ mA}, \text{ V}_{CB} = 12 \text{ V}, \\ f = 200 \text{ MHz} \end{array}$	3.0 15		dB

or (ed) **2N5770**



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